

DHG30I600PA

preliminary

600 V V_{RRM} =

I_{FAV} 30 A

40 ns

Sonic Fast Recovery Diode

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Part number

DHG30I600PA



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

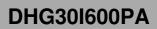
to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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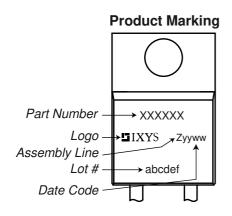
Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ing voltage	$T_{VJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			600	٧
I _R	reverse current, drain current	$V_R = 600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			50	μΑ
		$V_R = 600 \text{ V}$	$T_{VJ} = 125^{\circ}C$			2	mΑ
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			2.27	V
		$I_F = 60 \text{ A}$				3.14	٧
		$I_F = 30 \text{ A}$	T _{vJ} = 125°C			2.24	٧
		$I_F = 60 \text{ A}$				3.23	٧
I _{FAV}	average forward current	$T_c = 85^{\circ}C$	T _{vJ} = 150°C			30	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		T _{vJ} = 150°C			1.17	٧
r _F	slope resistance } for power lo	ess calculation only				32	mΩ
R _{thJC}	thermal resistance junction to case	е				0.7	K/W
R _{thCH}	thermal resistance case to heatsir	nk			0.50		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			180	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			200	Α
CJ	junction capacitance	$V_R = 400 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		16		pF
I _{RM}	max. reverse recovery current	<u> </u>	$T_{VJ} = 25 ^{\circ}\text{C}$		13		Α
		$I_F = 30 \text{ A}; V_R = 300 \text{ V}$	T _{vJ} = 125°C		17		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 30 \text{ A}; V_R = 300 \text{ V} \\ -di_F /dt = 600 \text{ A}/\mu\text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		40		ns
		,	T _{vJ} = 125°C		60		ns



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Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal			35	Α
T _{VJ}	virtual junction temperature		-55	5	150	°C
T _{op}	operation temperature		-55	5	125	°C
T _{stg}	storage temperature		-55	5	150	°C
Weight				2		g
M _D	mounting torque		0.4		0.6	Nm
F_c	mounting force with clip		20)	60	Ν



Part description

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast

30 = Current Rating [A] I = Single Diode

600 = Reverse Voltage [V]

PA = TO-220AC (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG30I600PA	DHG30I600PA	Tube	50	504019

Similar Part	Package	Voltage class
DHG30I600HA	TO-247AD (2)	600
DHG30IM600PC	TO-263AB (D2Pak) (2)	600

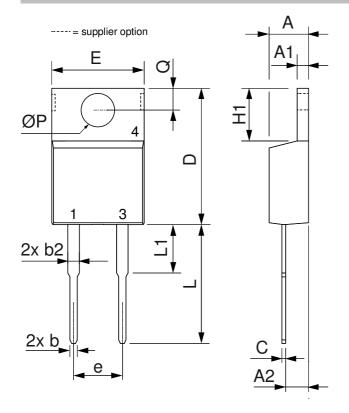
Equivalent Circuits for Simulation			* on die level	T _{vJ} = 150 °C
$I \rightarrow V_0$)— <u>R</u> o	Fast Diode		
V _{0 max}	threshold voltage	1.17		V
$R_{0 max}$	slope resistance *	29		$m\Omega$



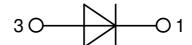


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Outlines TO-220



Dim.	Millimeter		Inches		
	Min.	Max.	Min.	Max.	
Α	4.32	4.82	0.170	0.190	
A1	1.14	1.39	0.045	0.055	
A2	2.29	2.79	0.090	0.110	
b	0.64	1.01	0.025	0.040	
b2	1.15	1.65	0.045	0.065	
С	0.35	0.56	0.014	0.022	
D	14.73	16.00	0.580	0.630	
E	9.91	10.66	0.390	0.420	
е	5.08	BSC	0.200	BSC	
H1	5.85	6.85	0.230	0.270	
L	12.70	13.97	0.500	0.550	
L1	2.79	5.84	0.110	0.230	
ØP	3.54	4.08	0.139	0.161	
Q	2.54	3.18	0.100	0.125	



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Fast Diode

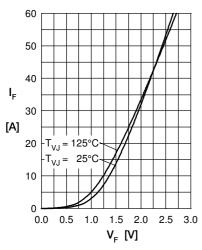


Fig. 1 Typ. Forward current versus V_F

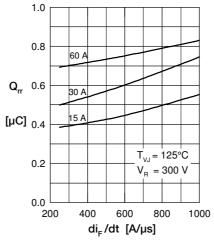


Fig. 2 Typ. reverse recov. charge Q_{rr} versus di/dt

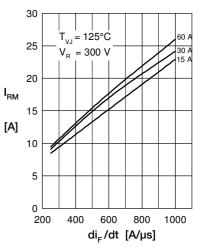


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

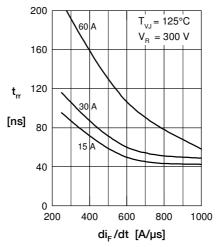
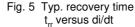
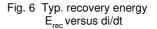


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}





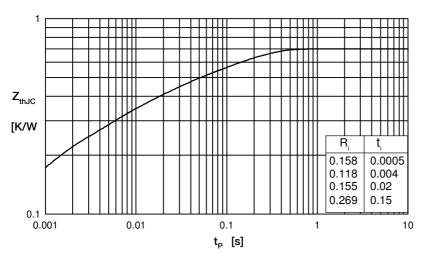


Fig. 7 Typ. transient thermal impedance junction to case